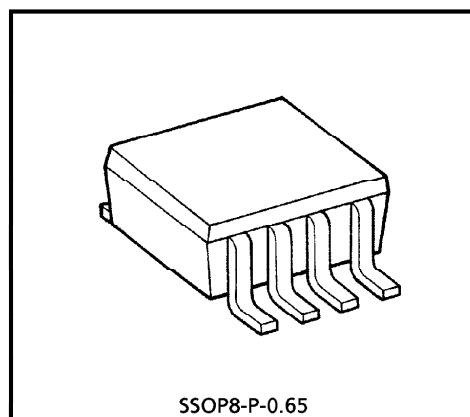


# TC7WH32FU

(UNDER DEVELOPMENT)

## DUAL 2-INPUT OR GATE

The TC7WH32FU is an advanced high speed CMOS 2-INPUT OR GATE fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 4 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.



Weight : 0.02g (Typ.)

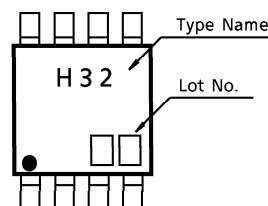
### FEATURES

- High Speed .....  $t_{pd} = 3.8ns$  (Typ.) at  $V_{CC} = 5V$
- Low Power Dissipation .....  $I_{CC} = 2\mu A$  (Max.) at  $T_a = 25^\circ C$
- High Noise Immunity .....  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays .....  $t_{pLH} = t_{pHL}$
- Wide Operating Voltage Range...  $V_{CC} (opr) = 2 \sim 5.5V$

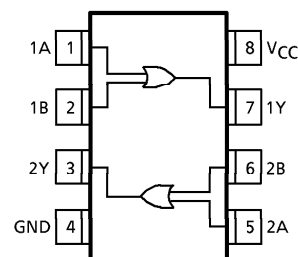
### MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	$V_{CC}$	$-0.5 \sim 7.0$	V
DC Input Voltage	$V_{IN}$	$-0.5 \sim 7.0$	V
DC Output Voltage	$V_{OUT}$	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	$-20$	mA
Output Diode Current	$I_{OK}$	$\pm 20$	mA
DC Output Current	$I_{OUT}$	$\pm 25$	mA
DC $V_{CC}$ / Ground Current	$I_{CC}$	$\pm 50$	mA
Power Dissipation	$P_D$	200	mW
Storage Temperature	$T_{stg}$	$-65 \sim 150$	$^\circ C$
Lead Temperature (10 s)	$T_L$	260	$^\circ C$

### MARKING



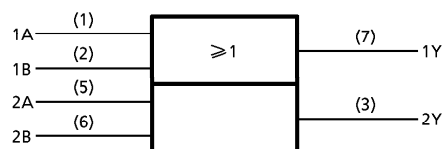
### PIN ASSIGNMENT (TOP VIEW)



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## LOGIC DIAGRAM



## TRUTH TABLE

A	B	Y
H	H	H
L	H	H
H	L	H
L	L	L

## RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	$V_{CC}$	2.0~5.5	V
Input Voltage	$V_{IN}$	0~5.5	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$dt/dv$	0~100 ( $V_{CC} = 3.3 \pm 0.3V$ )	ns/V
		0~20 ( $V_{CC} = 5 \pm 0.5V$ )	

## DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^\circ C$			$T_a = -40 \sim 85^\circ C$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	$V_{IH}$	—	2.0	1.50	—	—	1.50	—	V
			3.0~5.5	$V_{CC} \times 0.7$	—	—	$V_{CC} \times 0.7$	—	
Low-Level Input Voltage	$V_{IL}$	—	2.0	—	—	0.50	—	0.50	V
			3.0~5.5	—	—	$V_{CC} \times 0.3$	—	$V_{CC} \times 0.3$	
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -50 \mu A$	2.0	1.9	2.0	—	1.9	V
				3.0	2.9	3.0	—	2.9	
				4.5	4.4	4.5	—	4.4	
			$I_{OH} = -4mA$	3.0	2.58	—	—	2.48	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IL}$	$I_{OL} = 50 \mu A$	2.0	—	0.0	0.1	—	V
				3.0	—	0.0	0.1	—	
				4.5	—	0.0	0.1	—	
			$I_{OL} = 4mA$	3.0	—	—	0.36	—	
Input Leakage Current	$I_{IN}$	$V_{IN} = 5.5V$ or GND	$I_{OL} = 8mA$	4.5	—	—	0.36	—	$\mu A$
				0~5.5	—	—	$\pm 0.1$	—	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	2.0	—	20.0	$\mu A$

AC ELECTRICAL CHARACTERISTICS (Input  $t_r = t_f = 3\text{ns}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = - 40~85°C		UNIT
			V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t <sub>pLH</sub> t <sub>pHL</sub>	—	3.3 ± 0.3	15	—	5.5	7.9	1.0	9.5	ns
				50	—	8.0	11.4	1.0	13.0	
			5.0 ± 0.5	15	—	3.8	5.5	1.0	6.5	
				50	—	5.3	7.5	1.0	8.5	
Input Capacitance	C <sub>IN</sub>	—			—	4	10	—	10	pF
Power Dissipation Capacitance	C <sub>PD</sub>	(Note 1)			—	15	—	—	—	pF

(Note 1) : C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

NOISE CHARACTERISTICS (Ta = 25°C, Input  $t_r = t_f = 3\text{ns}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	TYP.	LIMIT	UNIT
Quiet Output Maximum Dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50pF	5.0	0.3	0.8	V
Quiet Output Minimum Dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50pF	5.0	− 0.3	− 0.8	V
Minimum High Level Dynamic Input Voltage	V <sub>IHD</sub>	C <sub>L</sub> = 50pF	5.0	—	3.5	V
Maximum Low Level Dynamic Input Voltage	V <sub>ILD</sub>	C <sub>L</sub> = 50pF	5.0	—	1.5	V

## INPUT EQUIVALENT CIRCUIT

